

THE UNITED STATES PATENT AND TRADEMARK OFFICE

**REVOCATION AND NEW POWER OF ATTORNEY AND  
CHANGE OF CORRESPONDENCE ADDRESS**

I, *Dr. Graham Fisher, Director of Intellectual Property of MEMC Electronic Materials, Inc.*, the Assignee of the entire right, title, and interest in the *U.S. Patent Application(s) and/or Patent(s) identified on the attached Schedule A*, hereby revoke all previous powers of attorney or authorizations of agent given and do hereby appoint the attorneys or agents associated with the following Customer Number, with full power of substitution and revocation, to prosecute and transact all business in the Patent and Trademark Office connected therewith for the *U.S. Patent Application(s) and/or Patent(s) listed in the attached Schedule A*:

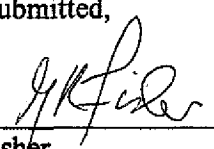
*Customer Number: 76681*

Please direct all correspondence in connection with said *U.S. Patent Application(s) and/or Patent(s)* to:

*Customer Number: 76681*

Respectfully submitted,

Date: 5/13/2008

  
\_\_\_\_\_  
Dr. Graham Fisher  
Director of Intellectual Property  
MEMC Electronic Materials, Inc.

PATENT

THE UNITED STATES PATENT AND TRADEMARK OFFICE

STATEMENT UNDER 37 CFR 3.73(b)

**MEMC Electronic Materials, Inc.**, a Delaware Corporation, pursuant to 37 CFR 3.73(b), hereby states that it is the Assignee of the entire right, title, and interest in *U.S. Patent Application(s) and/or Patent(s) on the attached Schedule A.*

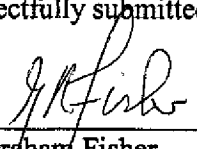
The entire rights, title, and interest in the aforementioned Patent Application(s) and/or Patent(s) were conveyed to **MEMC Electronic Materials, Inc.** via Assignment(s) recorded with the United States Patent and Trademark Office at the *Reel/Frame Numbers on the attached Schedule A.*

The undersigned, **Dr. Graham Fisher, Director of Intellectual Property**, has full authorization to act on behalf of Assignee **MEMC Electronic Materials, Inc.**

Respectfully submitted,

Date: \_\_\_\_\_

5/13/2008

  
\_\_\_\_\_  
Dr. Graham Fisher  
Director of Intellectual Property  
MEMC Electronic Materials, Inc.

# **APPENDIX A** **Owned by MEMC Electronic Materials, Inc.**

ATTORNEY REFERENCE	CONF. NO	PUBLICATION NO. & DATE	SERIAL NO. FILING DATE	PATENT NO. ISSUE DATE	CURRENT OWNER/ ASSIGNEE	REEL AND FRAME NO.	TITLE
28744-177 (MEMC3114.1)	4497	US2007-0045738-A1 3/1/2007	11/461,956 8/2/2006		MEMC Electronic Materials, Inc.	018400/0468	METHOD FOR THE MANUFACTURE OF A STRAINED SILICON-ON-INSULATOR STRUCTURE
28744-60 (MEMC3115.1)	3973	US2007-0042586-A1 2/22/2007	11/461,853 8/1/2006		MEMC Electronic Materials, Inc.	018486/0347	STRAINED SILICON ON INSULATOR (SSOI) STRUCTURE WITH IMPROVED CRYSTALLINITY IN THE STRAINED SILICON LAYER
28744-155 (MEMC3116)	5718	US 2006-0231035 A1 10/19/2006	11/107,444 4/15/2005		MEMC Electronic Materials, Inc.	016278/0974	MODIFIED SUSCEPTOR FOR BARREL REACTOR
28744-346 (MEMC3126)	9475	US-2007-0249136-A1 10/25/2007	11/408,503 4/21/2006		MEMC Electronic Materials, Inc.	017974/0835	SILICON STRUCTURES WITH IMPROVED RESISTANCE TO RADIATION EVENTS
28744-347 (MEMC3127.1)	4131	US2007-0179659-A1 8/2/2007	11/617,430 12/28/2006		MEMC Electronic Materials, Inc.	019136/0568	DOUBLE SIDE WAFER GRINDER AND METHODS FOR ASSESSING WORKPIECE NANOTOPOLOGY
28744-349 (MEMC3128.1)	5925	US2007-0176238-A1 8/12/2007	11/698,728 1/26/2007		MEMC Electronic Materials, Inc.	019110/0543	SILICON WAFER WITH HIGH THERMAL CONDUCTIVITY
28744-351 (MEMC3131.1)	2048	US2007-0178807-A1 8/12/2007	11/621,920 1/10/2007		MEMC Electronic Materials, Inc.	019177/0655	WIRE SAW INGOT SLICING SYSTEM AND METHOD WITH INGOT PREHEATING, WEB PREHEATING, SLURRY TEMPERATURE CONTROL AND/OR SLURRY FLOW RATE CONTROL
MEMC3139	2638		11/616,485 12/27/2006		MEMC Electronic Materials, Inc.	019686/0657	WAFER SUPPORT AND METHOD OF MAKING WAFER SUPPORT
28744-63 (MEMC3151)	2685	US2007-0117350-A1 5/24/2007	11/616,517 12/27/2006		MEMC Electronic Materials, Inc.	018823/0530	STRAINED SILICON ON INSULATOR (SSOI) WITH LAYER TRANSFER FROM OXIDIZED DONOR
28744-147 (MEMC3152)	8867		11/614,129 12/21/2006		MEMC Electronic Materials, Inc.	019935/0398	METHOD OF POLISHING A SEMICONDUCTOR WAFER
28744-354 (MEMC3155)	4137	US2007-0179660-A1 8/12/2007	11/617,433 12/28/2006		MEMC Electronic Materials, Inc.	019136/0619	DOUBLE SIDE WAFER GRINDER AND METHODS FOR ASSESSING WORKPIECE NANOTOPOLOGY
28744-170 (MEMC972703.1)	5307	US2007-0224783-A1 9/27/2007	11/753,294 5/24/2007		MEMC Electronic Materials, Inc.	Continuation of 11/058,996 recorded at 9409/0291	PROCESS FOR FORMING LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON
28744-356 (MEMC980411.1)	2920	US2007-0238286-A1 10/11/2007	11/763,043 6/14/2007		MEMC Electronic Materials, Inc.	Division of 10/911,965 recorded at 010225/0266	NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES
28744-357 (MEMC983053.1)	8402	US-2008-0020168-A1 1/24/2008	11/833,730 8/3/2007		MEMC Electronic Materials, Inc.	Continuation of 10/963,137 which is a continuation of 10/038,084 recorded at 010449/0840	SILICON ON INSULATOR STRUCTURE WITH A SINGLE CRYSTAL CZ SILICON DEVICE LAYER HAVING A REGION WHICH IS FREE OF AGGLOMERATED INTRINSIC POINT DEFECTS
28744-340 (MEMC3094.8)	1290	US-2008-0020684-A1 1/24/2008	10/598,851 5/10/2007		MEMC Electronic Materials, Inc.	U.S. National of PCT based on provisional 60/554,684 recorded at 015315/0827 and 015263/0403	WAFER CLAMPING DEVICE FOR A DOUBLE SIDE GRINDER